



# GT600CH120T9H-M

## IGBT Module

Preliminary Data

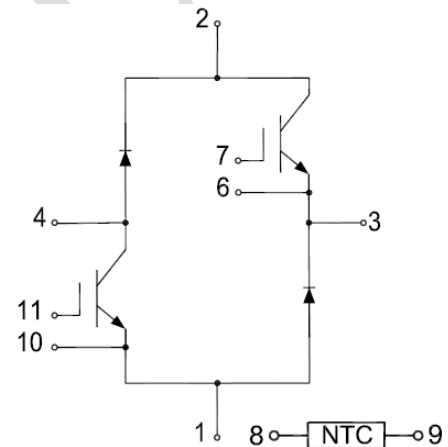
### Features:

- Trench & Field Stop IGBT
- Short Circuit Rated >10 $\mu$ s
- Low Switching Loss
- 100% RBSOA Tested(2xIc)
- Low Stray Inductance
- Lead Free, Compliant with RoHS Requirement



### Applications:

- UPS Systems
- Servo Applications
- Motor Drives
- Medical Applications
- High Frequency Switching Applications



### Chopper IGBT

Maximum Rated Values of Chopper IGBT ( $T_C=25^\circ\text{C}$  unless otherwise specified)

$V_{CES}$	Collector-Emitter Blocking Voltage		1200	V
$V_{GES}$	Gate-Emitter Voltage		$\pm 20$	V
$I_C$	Continuous Collector Current	$T_C=100^\circ\text{C}$	600	A
		$T_C=25^\circ\text{C}$	1160	A
$I_{CM}$	Peak Collector Current Repetitive	$T_J=175^\circ\text{C}$	1200	A
$t_{SC}$	Short Circuit Withstand Time		>10	$\mu\text{s}$
$P_D$	Maximum Power Dissipation (IGBT)	$T_C=25^\circ\text{C}$ $T_{Jmax}=175^\circ\text{C}$	3950	W



## Electrical Characteristics of Chopper IGBT ( $T_C=25^\circ\text{C}$ unless otherwise specified)

### Static Characteristics

Symbol	Description	Conditions	Min	Typ	Max	Unit
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=10\text{mA}$ , $V_{CE}=V_{GE}$	5.0	5.5	6.8	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=600\text{A}$ , $V_{GE}=15\text{V}$	$T_J=25^\circ\text{C}$	1.70	1.95	V
			$T_J=125^\circ\text{C}$	1.90		V
			$T_J=150^\circ\text{C}$	2.00		V
$I_{CES}$	Collector-Emitter Leakage Current	$V_{GE}=0\text{V}$ , $V_{CE}=V_{CES}$ , $T_J=25^\circ\text{C}$			1	mA
$I_{GES}$	Gate-Emitter Leakage Current	$V_{GE}=\pm 20\text{V}$ , $V_{CE}=0\text{V}$ , $T_J=25^\circ\text{C}$			800	nA
$C_{ies}$	Input Capacitance			49.26		nF
$C_{oes}$	Output Capacitance	$V_{CE}=25\text{V}$ , $V_{GE}=0\text{V}$ , $f=1\text{MHz}$		3.67		nF
$C_{res}$	Reverse Transfer Capacitance			1.85		nF

### Switching Characteristics

$t_{d(on)}$	Turn-on Delay Time	$V_{CC}=600\text{V}$ , $I_C=600\text{A}$ , $R_{Gon}=1\Omega$ , $V_{GE}=\pm 15\text{V}$ , Inductive Load	$T_J=25^\circ\text{C}$	0.55		$\mu\text{s}$
			$T_J=125^\circ\text{C}$	0.56		
			$T_J=150^\circ\text{C}$	0.56		
$t_r$	Rise Time		$T_J=25^\circ\text{C}$	0.22		$\mu\text{s}$
			$T_J=125^\circ\text{C}$	0.22		
			$T_J=150^\circ\text{C}$	0.23		
$t_{d(off)}$	Turn-off Delay Time		$T_J=25^\circ\text{C}$	0.54		$\mu\text{s}$
			$T_J=125^\circ\text{C}$	0.57		
			$T_J=150^\circ\text{C}$	0.57		
$t_f$	Fall Time	$T_J=25^\circ\text{C}$	0.14		$\mu\text{s}$	
		$T_J=125^\circ\text{C}$	0.18			
		$T_J=150^\circ\text{C}$	0.19			
$E_{on}$	Turn-on Switching Loss	$V_{CC}=600\text{V}$ , $I_C=600\text{A}$ , $R_{Gon}=1\Omega$ , $V_{GE}=\pm 15\text{V}$ , $di/dt=2120\text{A}/\mu\text{s}$ ( $T_J=150^\circ\text{C}$ ) Inductive Load	$T_J=25^\circ\text{C}$	49.0		mJ
			$T_J=125^\circ\text{C}$	75.8		
			$T_J=150^\circ\text{C}$	81.2		



E <sub>off</sub>	Turn-off Switching Loss	V <sub>CC</sub> =600V, I <sub>C</sub> =600A, R <sub>Goff</sub> =1Ω, V <sub>GE</sub> = ±15V, du/dt=2600V/μs (T <sub>J</sub> =150°C) Inductive Load	T <sub>J</sub> =25°C	81.5	mJ
			T <sub>J</sub> =125°C	96.1	
			T <sub>J</sub> =150°C	100.1	
Q <sub>g</sub>	Total Gate Charge	V <sub>GE</sub> =+15V...-15V	T <sub>J</sub> =25°C	3.36	μC
R <sub>g internal</sub>	Internal Gate Resistance		T <sub>J</sub> =25°C	1.1	Ω
RBSOA	I <sub>C</sub> =1200A, V <sub>CC</sub> =1050V, V <sub>p</sub> =1200V, R <sub>G</sub> = 1Ω, V <sub>GE</sub> =+15V to 0V, T <sub>J</sub> =150°C			Trapezoid	
SCSOA	V <sub>CC</sub> =600V, V <sub>GE</sub> =15V, T <sub>J</sub> =150°C			10	μs
R <sub>θJC</sub>	IGBT Thermal Resistance: Junction-To-Case(per leg)			0.038	°C/W

## Chopper Diode

### Maximum Rated Values of Chopper Diode (T<sub>C</sub>=25°C unless otherwise specified)

V <sub>RRM</sub>	Repetitive Peak Reverse Voltage	1200	V
I <sub>F</sub>	Diode Continuous Forward Current	600	A
I <sub>FM</sub>	Diode Maximum Forward Current	1200	A

### Electrical Characteristics of Chopper Diode (T<sub>C</sub>=25°C unless otherwise specified)

Symbol	Description	Conditions	Min	Typ	Max	Unit	
V <sub>FM</sub>	Forward Voltage	I <sub>F</sub> =600A	T <sub>J</sub> =25°C		1.80	2.00	V
			T <sub>J</sub> =125°C		1.90		
			T <sub>J</sub> =150°C		1.90		
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> =600A, -diF/dt=2270A/μs(T <sub>J</sub> =150°C), V <sub>R</sub> =600V, V <sub>GE</sub> =-15V	T <sub>J</sub> =25°C		0.37		μs
			T <sub>J</sub> =125°C		0.58		
			T <sub>J</sub> =150°C		0.65		
I <sub>rr</sub>	Peak Reverse Recovery Current	I <sub>F</sub> =600A, -diF/dt=2270A/μs(T <sub>J</sub> =150°C), V <sub>R</sub> =600V, V <sub>GE</sub> =-15V	T <sub>J</sub> =25°C		238		A
			T <sub>J</sub> =125°C		294		
			T <sub>J</sub> =150°C		306		



Q <sub>rr</sub>	Reverse Recovery Charge	I <sub>F</sub> =600A, -diF/dt=2270A/μs(T <sub>J</sub> =150°C), V <sub>R</sub> =600V, V <sub>GE</sub> =-15V	T <sub>J</sub> =25°C	52.3	μC
			T <sub>J</sub> =125°C	96.1	
			T <sub>J</sub> =150°C	110.6	
E <sub>rec</sub>	Reverse Recovery Energy		T <sub>J</sub> =25°C	22.0	mJ
			T <sub>J</sub> =125°C	38.3	
			T <sub>J</sub> =150°C	44.6	
R <sub>θJC</sub>	Diode Thermal Resistance: Junction-To-Case (per leg)			0.064	°C/W

## Internal NTC-Thermistor Characteristics

Symbol	Description		Min.	Typ.	Max.	Units.
R <sub>25</sub>	Rated Resistance	T <sub>C</sub> =25°C		5		kΩ
ΔR/R	Deviation of R100	T <sub>C</sub> =100°C, R <sub>100</sub> =481Ω	-5		5	%
P <sub>25</sub>	Power Dissipation	T <sub>C</sub> =25°C			10	mW
B <sub>25/50</sub>	B-Value	$R_2=R_{25} \exp[B_{25/50}(1/T_2-1/(298.15K))]$		3380		K
B <sub>25/80</sub>	B-Value	$R_2=R_{25} \exp[B_{25/80}(1/T_2-1/(298.15K))]$		3440		K

## Module

Symbol	Description		Min.	Typ.	Max.	Units
V <sub>iso</sub>	Isolation Voltage (All Terminals Shorted)	RMS, f=50Hz, 1minute	2500			V
L <sub>sCE</sub>	Stray Inductance Module			20		nH
T <sub>J</sub>	Maximum Junction Temperature				150	°C
T <sub>JOP</sub>	Maximum Operating Junction Temperature Range		-40		+150	°C
T <sub>stg</sub>	Storage Temperature		-40		+125	°C
CTI	Comparative Tracking Index		200			
R <sub>θCS</sub>	Case-to-Sink Thermally (Conductive Grease Applied)				0.02	°C/W
M	Terminals Connection Torque	Screw M6-Mounting according to valid application note	3.0		6.0	N·m
M	Mounting Torque for Module Mounting	Screw M5--Mounting according to valid application note	3.0		6.0	N·m
G	Weight			330		g

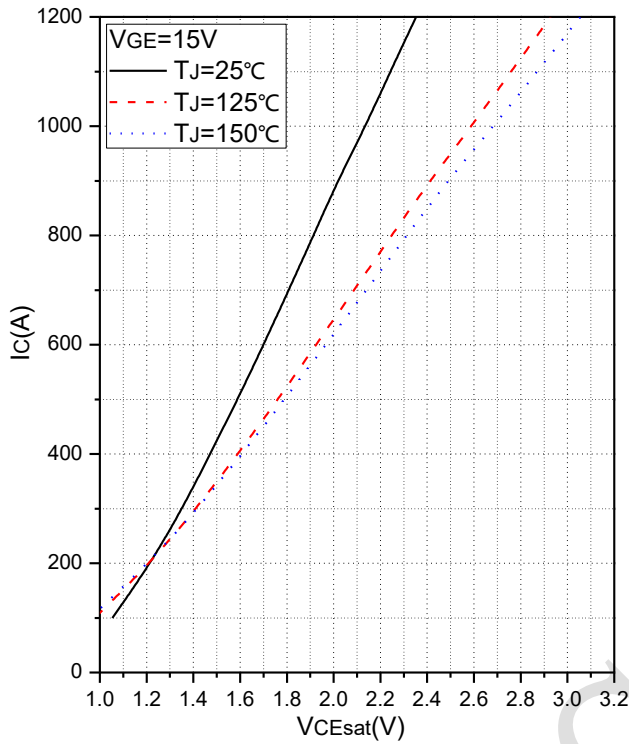


Fig.1 Typical Saturation Voltage Characteristics

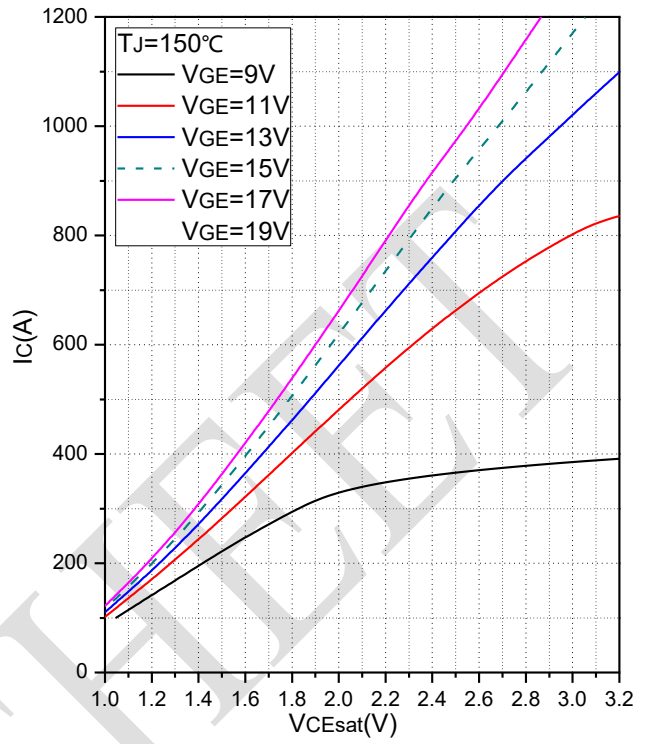


Fig.2 Typical Output Characteristics

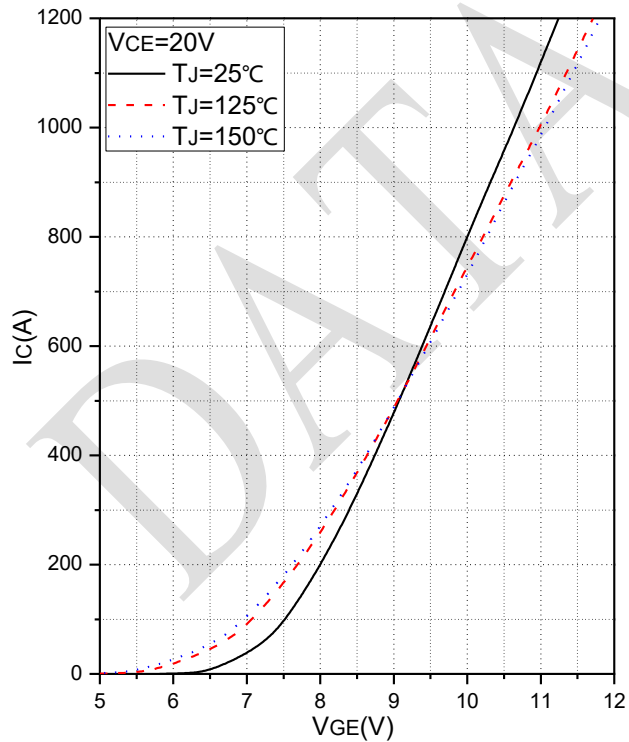


Fig.3 Transfer Characteristic

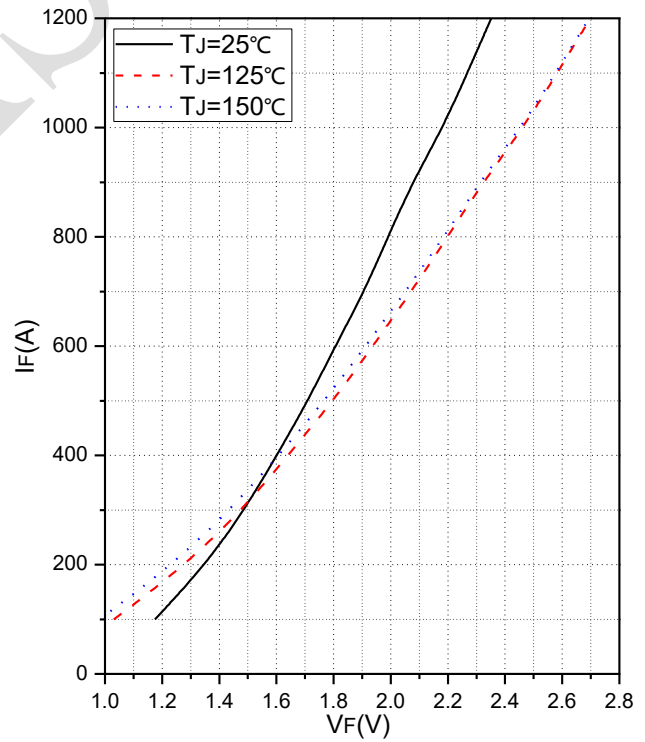


Fig.4 Forward Characteristics of Diode

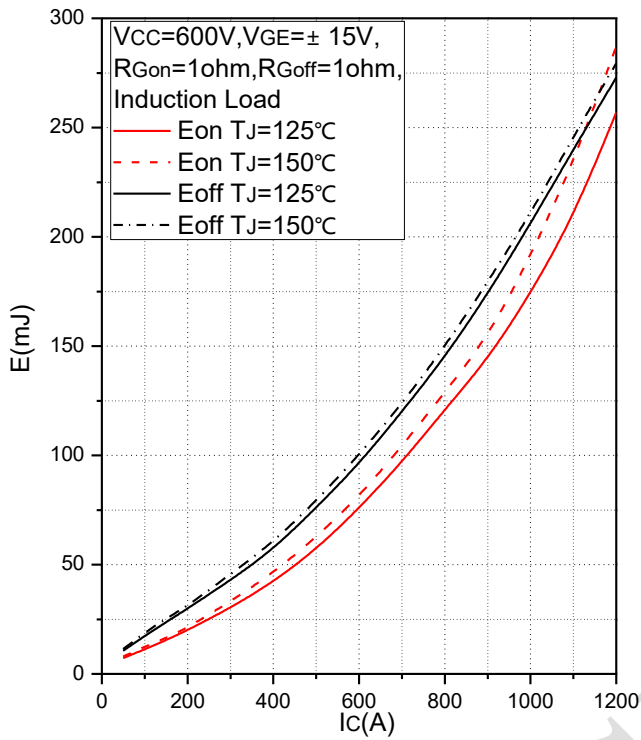


Fig.5 Typical Switching Loss vs. Collector Current

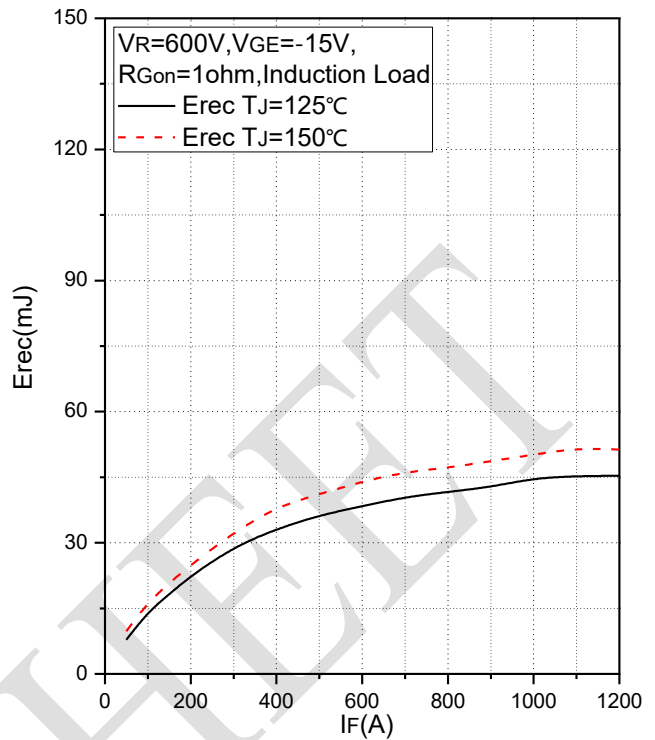


Fig.6 Typical Switching Loss vs. Forward Current

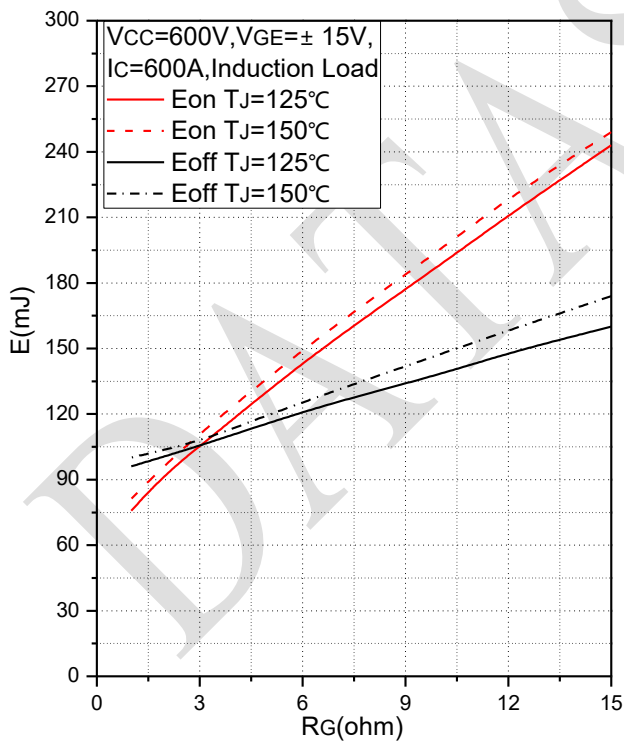


Fig.7 Typical Switching Loss vs. Gate Resistance

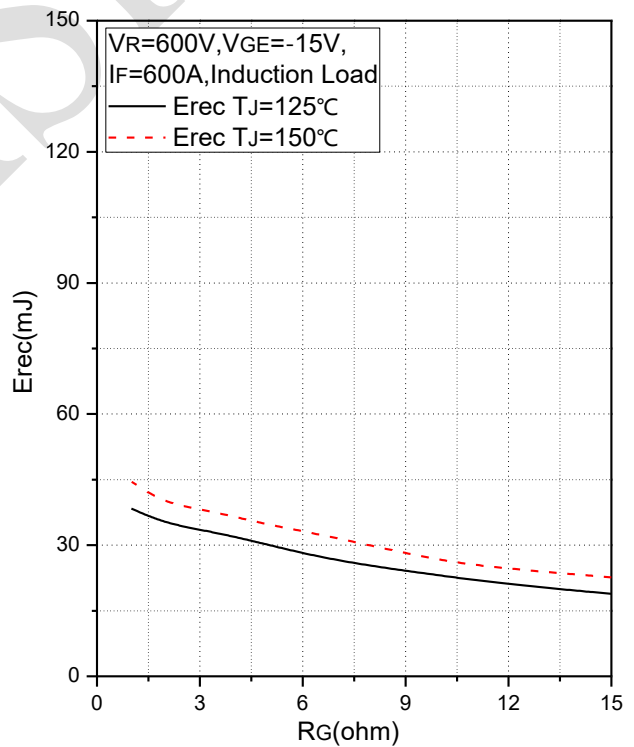


Fig.8 Typical Switching Loss vs. Gate Resistance

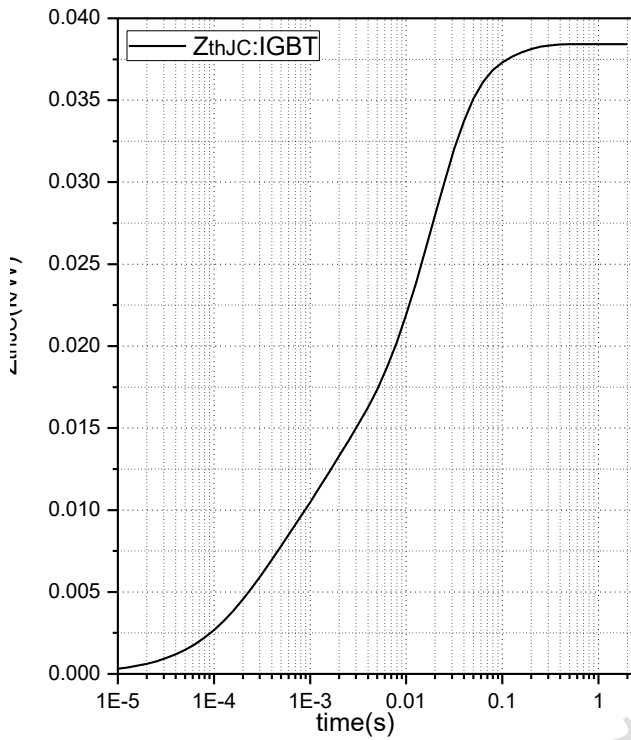


Fig.9 Transient Thermal Impedance (IGBT)

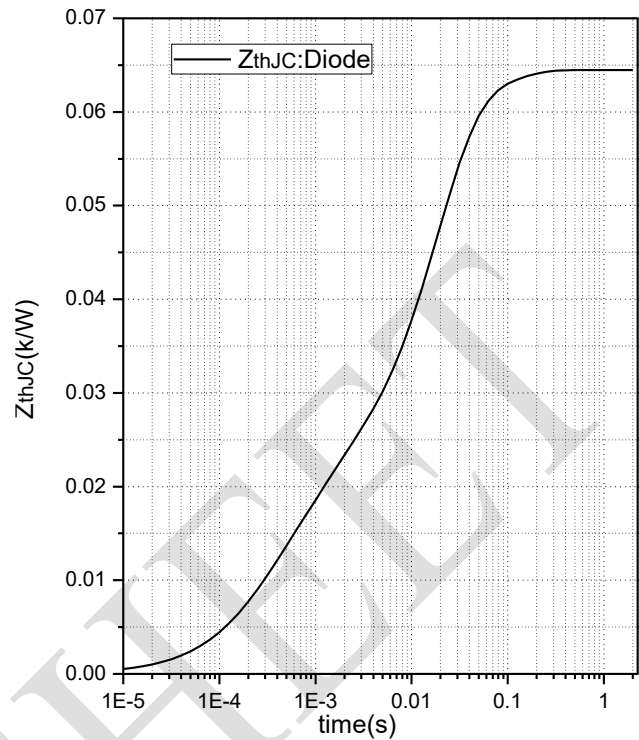


Fig.10 Transient Thermal Impedance (Diode)

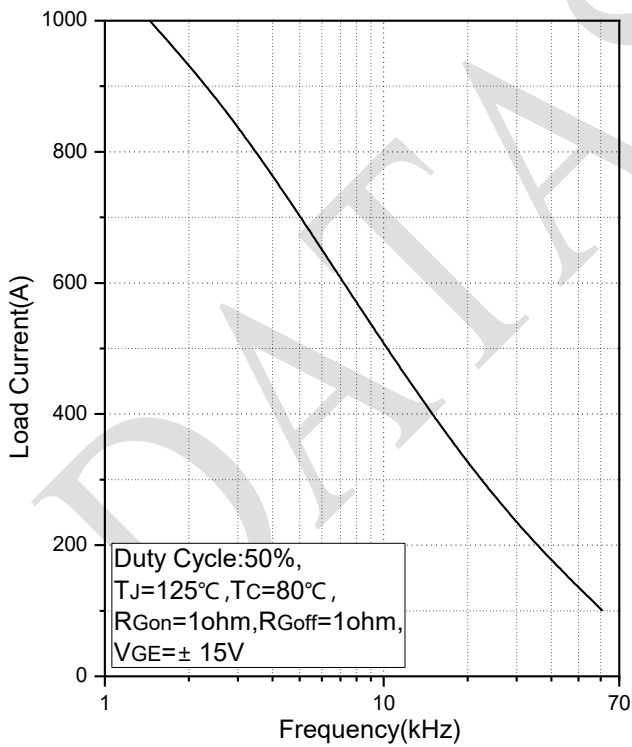


Fig.11 Typical Load Current vs. Frequency

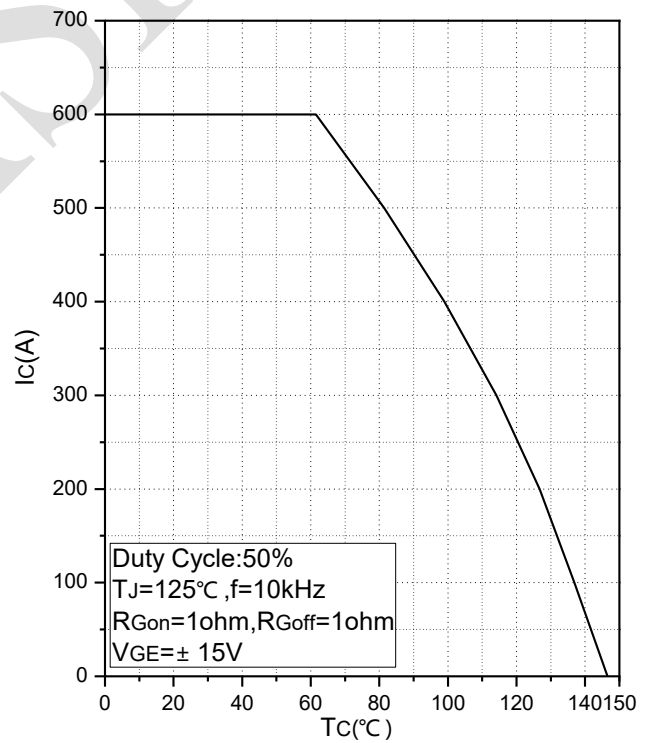


Fig.12 Rated Current vs. Temperature

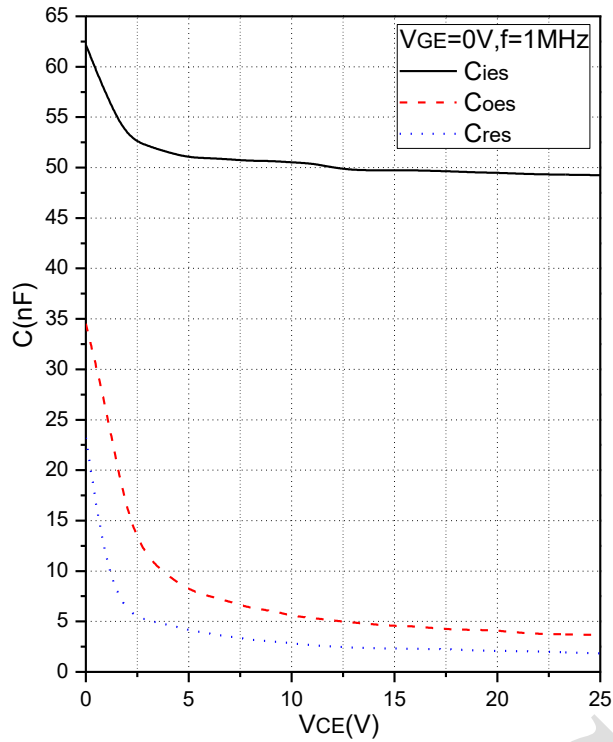


Fig.13 Capacitance Characteristics

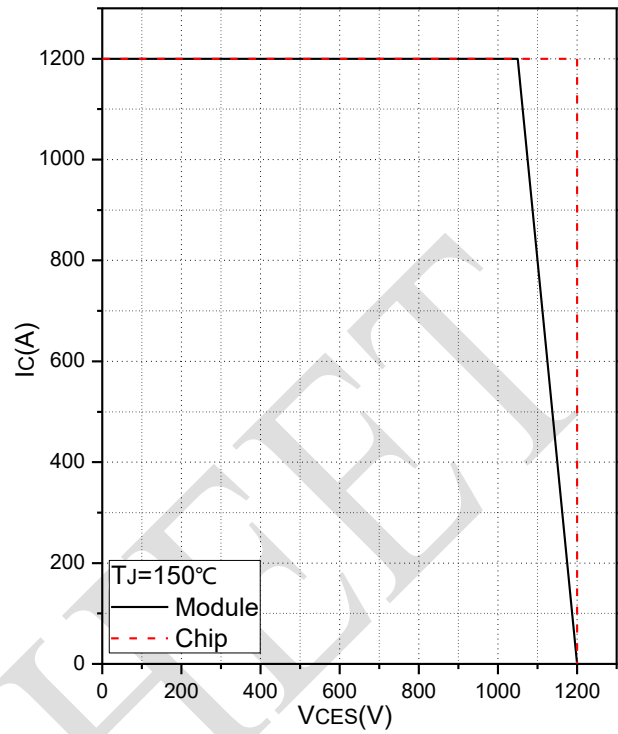


Fig.14 Reverse Bias Safe Operation Area (RBSOA)

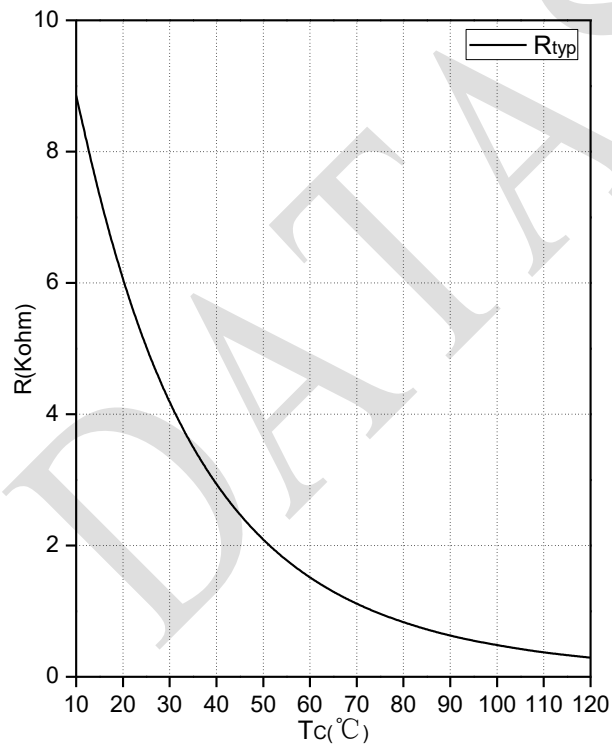


Fig.15 NTC Temperature Characteristics







Date	Revision	Notes
01/07/2020	01	Initial Release

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DATA SHEET